

DIE NO. 2C5551 — NPN

LINE SOURCE — DMB106

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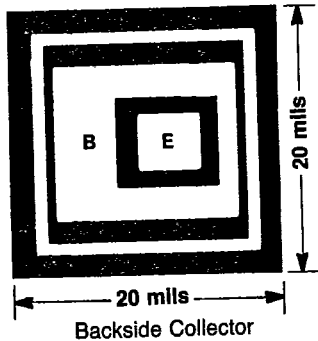
This die provides performance similar to that of the following device types:

2N4409
2N4410
2N4418*
2N5550
2N5551

MM3008
MM3009
MPS5135
MPSD02
MPSL01

Designed for high-voltage, general-purpose amplifier applications.

*No longer available



METALLIZATION —

Top Al
Back Au

BACKSIDE GOLD 3000Å

DIE THICKNESS 6 ± 2 mils

BONDING PAD SIZE —

Emitter 4.2×4.6 mils
Base 2.8×9.0 mils

GLASSIVATION — The die active area, except for bond windows, is covered with Glassivation to protect from contaminants and accidental bonding.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$; Note 1)

Parameter	Test Conditions	Min	Max	Unit
BV_{CEO}	$I_C = 1.0 \text{ mAdc}, I_B = 0$	160	—	Vdc
BV_{CBO}	$I_C = 100 \mu\text{Adc}, I_E = 0$	180	—	Vdc
BV_{EBO}	$I_E = 10 \mu\text{Adc}, I_C = 0$	6.0	—	Vdc
I_{CBO}	$V_{CB} = 120 \text{ Vdc}, I_E = 0$	—	50	nAdc
h_{FE}	$I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$	80	250	—

- NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 5\%$.
2. Detailed device characteristics are available from your Motorola sales representative.